

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:
David J. Keller

Serial No.: 09/458,875

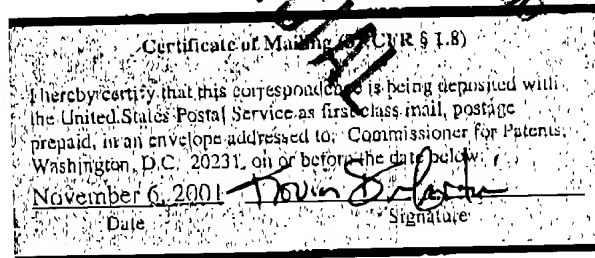
Filed: December 10, 1999

For: POLYSILICON ETCH USEFUL DURING THE
MANUFACTURE OF A SEMICONDUCTOR
DEVICE

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§ GAU: 1763
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§ Examiner: George Goudreau
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§ Atty. Docket: 99-0738.00
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Commissioner for Patents
Washington, D.C. 20231



RESPONSE TO THE OFFICE ACTION OF JULY 6, 2001

Please enter the following in response to the Examiner's outstanding office action of July 6, 2001.

In the Specification

Please delete the paragraph on page 8 lines 9-13 and insert the following new paragraph therefore:

-- FIG. 6 depicts an etch using a flow rate of 9 sccm HeO₂, 50 sccm HBr, 100 sccm He, 70 watts lower power, 350 watts upper power, a pressure of 60 mTorr, and a duration of 60 seconds. The resulting etch undercuts the polysilicon 60, especially toward the bottom of the feature. The upper portion of the polysilicon 60 remains substantially vertical. This etch removes the polysilicon at a faster isotropic rate than the etch described with reference to FIG. 5. --